

L Number	Hits	Search Text	DB	Time stamp
1	44271	sic or (silicon adj carbide)	USPAT; US-PGPUB	2002/11/12 08:13
2	6785	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet))	USPAT; US-PGPUB	2002/11/12 08:13
3	373	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) and (anneal\$4 same ("h.sub.2" or hydrogen))	USPAT; US-PGPUB	2002/11/12 08:32
4	225	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	USPAT; US-PGPUB	2002/11/12 07:59
5	41	((sic or (silicon adj carbide)) same (anneal\$4 near12 ("h.sub.2" or hydrogen)))	USPAT; US-PGPUB	2002/11/12 08:13
6	25	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) and ((sic or (silicon adj carbide)) same (anneal\$4 near12 ("h.sub.2" or hydrogen)))	USPAT; US-PGPUB	2002/11/12 07:55
7	1163	((nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj oxide) or (nitric adj oxide) or nitrogenation) same (anneal\$4 near12 ("h.sub.2" or hydrogen)))	USPAT; US-PGPUB	2002/11/12 08:11
8	66	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) and ((nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj oxide) or (nitric adj oxide) or nitrogenation) same (anneal\$4 near12 ("h.sub.2" or hydrogen)))	USPAT; US-PGPUB	2002/11/12 08:01
10	0	((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or hydrogen))) and ((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet))	USPAT; US-PGPUB	2002/11/12 08:11
11	1	((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or hydrogen))) and (sic or (silicon adj carbide))	USPAT; US-PGPUB	2002/11/12 08:11
9	43	(oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or hydrogen))	USPAT; US-PGPUB	2002/11/12 08:12
12	56448	sic or (silicon adj carbide)	EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:13
13	5373	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet))	EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:36
14	12	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:13
15	20	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) same (anneal\$4 same ("h.sub.2" or hydrogen))	USPAT; US-PGPUB	2002/11/12 08:34
16	24	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) same ("n.sub.2 o")	USPAT; US-PGPUB	2002/11/12 08:35
17	2	((sic or (silicon adj carbide)) same (semiconductor or mos or mosfet)) same ("n.sub.2 o" or n2o)	EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:37